

■ PRODUCT CHARACTERISTICS

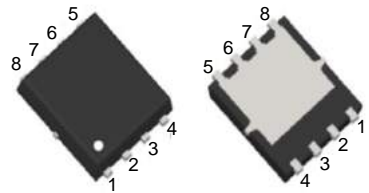
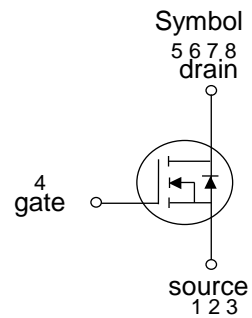
V <sub>DSS</sub>	40V
R <sub>DS(on)</sub> Typ(@V <sub>GS</sub> =4.5V)	9.5mΩ
R <sub>DS(on)</sub> Typ(@V <sub>GS</sub> =10V)	6.5mΩ
I <sub>D</sub>	60A

■ APPLICATIONS

DC/DC converter  
Ideal for high-frequency switching  
and synchronous rectification

■ FEATURES

Very low on-resistance R<sub>DS(on)</sub>  
Good stability and uniformity with high E<sub>AS</sub>  
Pb-free lead plating



PDFN5X6-8L

■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-free	Halogen		
N/A	MOT4180G	PDFN5X6-8L	5000pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS(T<sub>C</sub>=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V <sub>DSS</sub>	40	V
Gate-source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	60	A
Pulsed drain current	I <sub>DM</sub>	200	A
Avalanche energy single pulsed	E <sub>AS</sub>	400	mJ
Power dissipation	P <sub>D</sub>	40	W
Junction temperature	T <sub>J</sub>	+150	°C
Storage temperature	T <sub>STG</sub>	-55~ +175	°C

■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On characteristics						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	-	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	6.5	8.0	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	9.5	13	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =20A	10	-	-	S
Dynamic characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1.0MHz	-	1800	-	pF
Output Capacitance	C <sub>oss</sub>		-	280	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	190	-	pF
Switching characteristics						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, I <sub>D</sub> =2A, R <sub>L</sub> =1Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	6.4	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	17.2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	29.6	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	16.8	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	29	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	6.4	-	nC
Drain-source diode characteristics						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =10A	-	-	1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	60	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A di/dt = 100A/μs	-	29	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	26	-	nS

■ TYPICAL CHARACTERISTICS

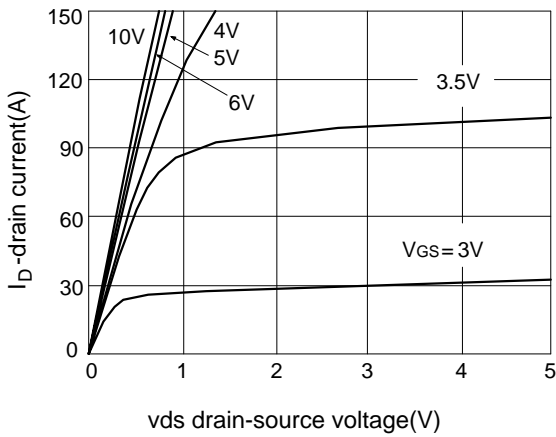


Fig.1 output characteristics

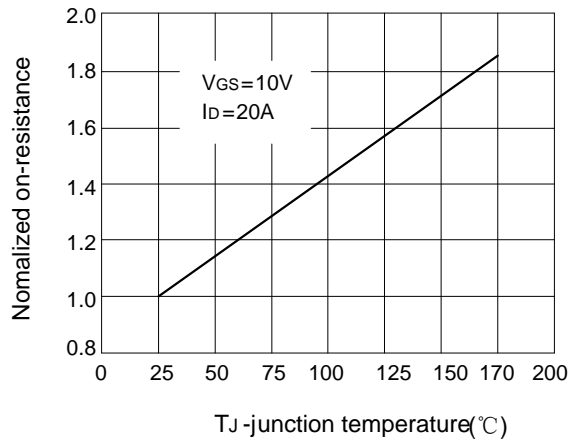


Fig.2 rdson-junction temperature

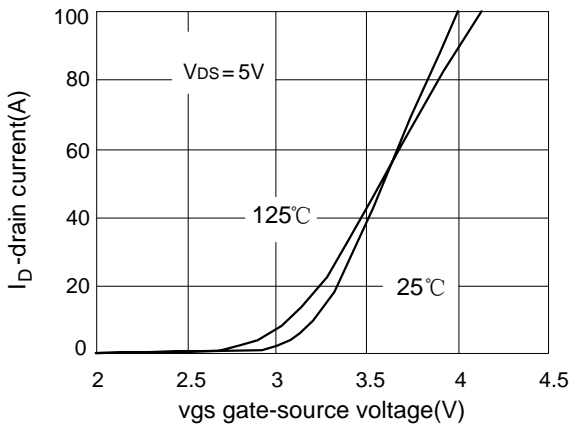


Fig.3 transfer characteristics

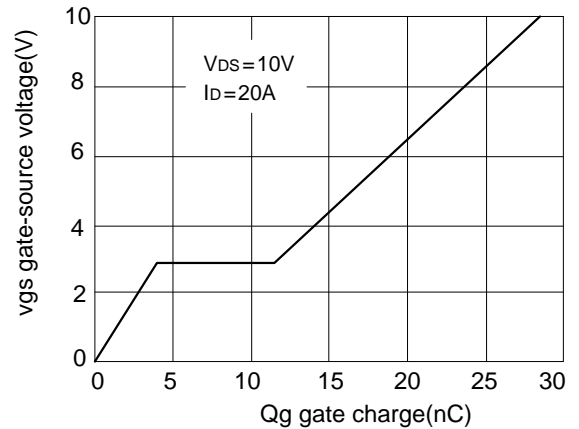


Fig.4 gate charge

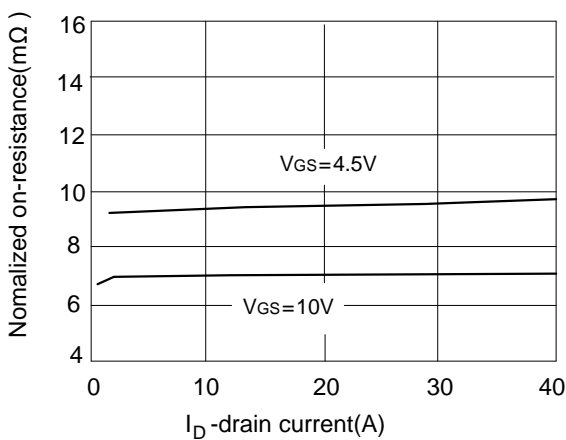


Fig.5 rdson-drain current

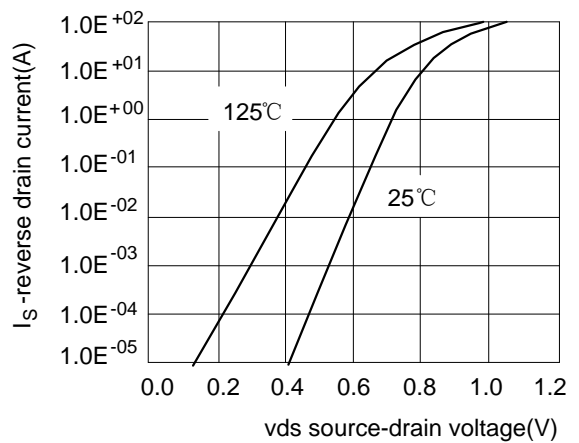


Fig.6 source-drain diode forward

■ TYPICAL CHARACTERISTICS(Cont.)

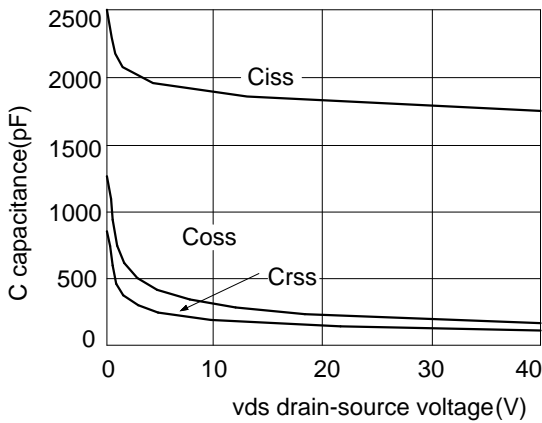


Fig.7 capacitance vs vds

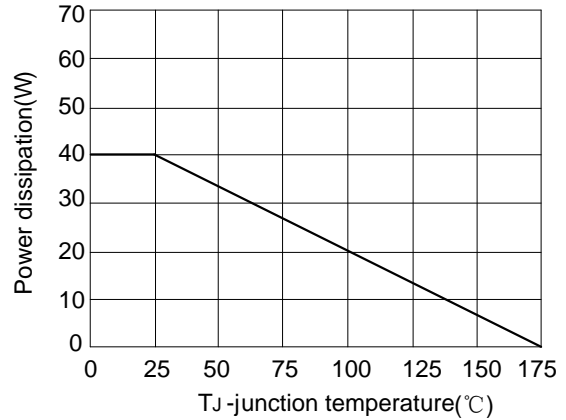


Fig.8 power de-rating

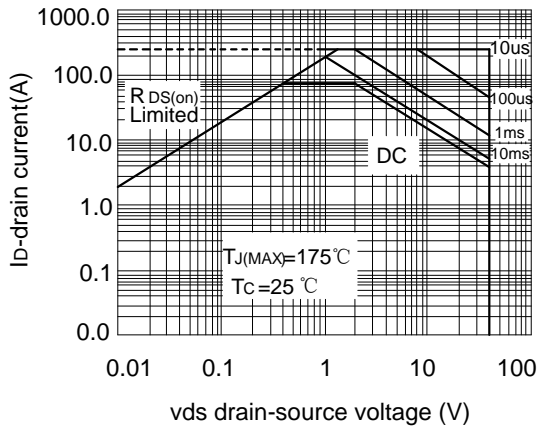


Fig.9 safe operation area

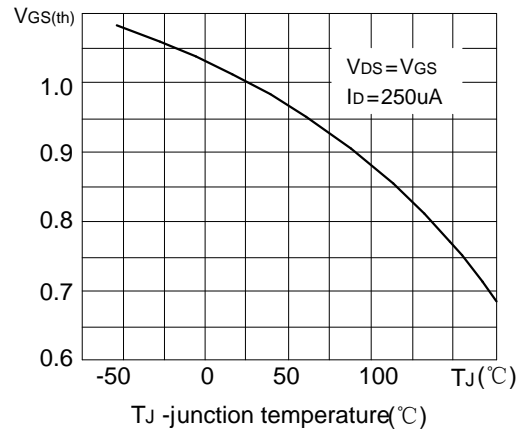


Fig.10 VGS(th) vs junction temperature

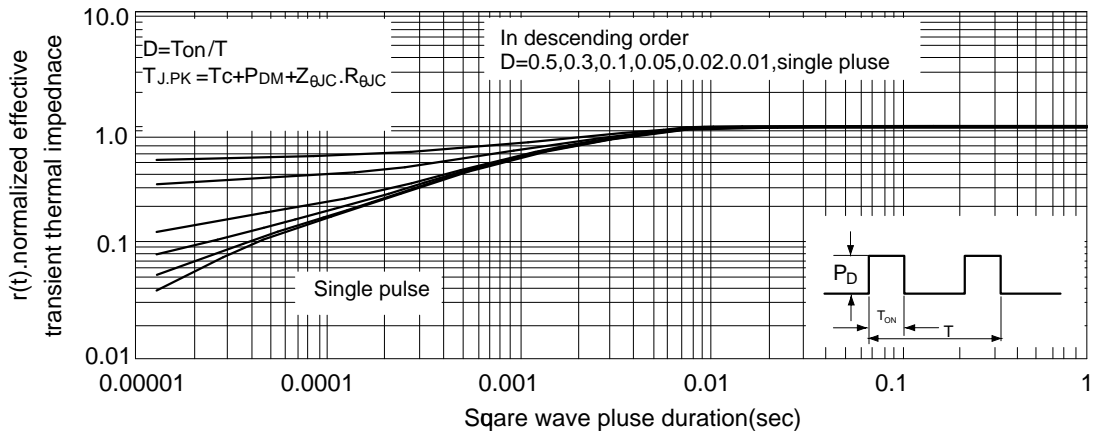
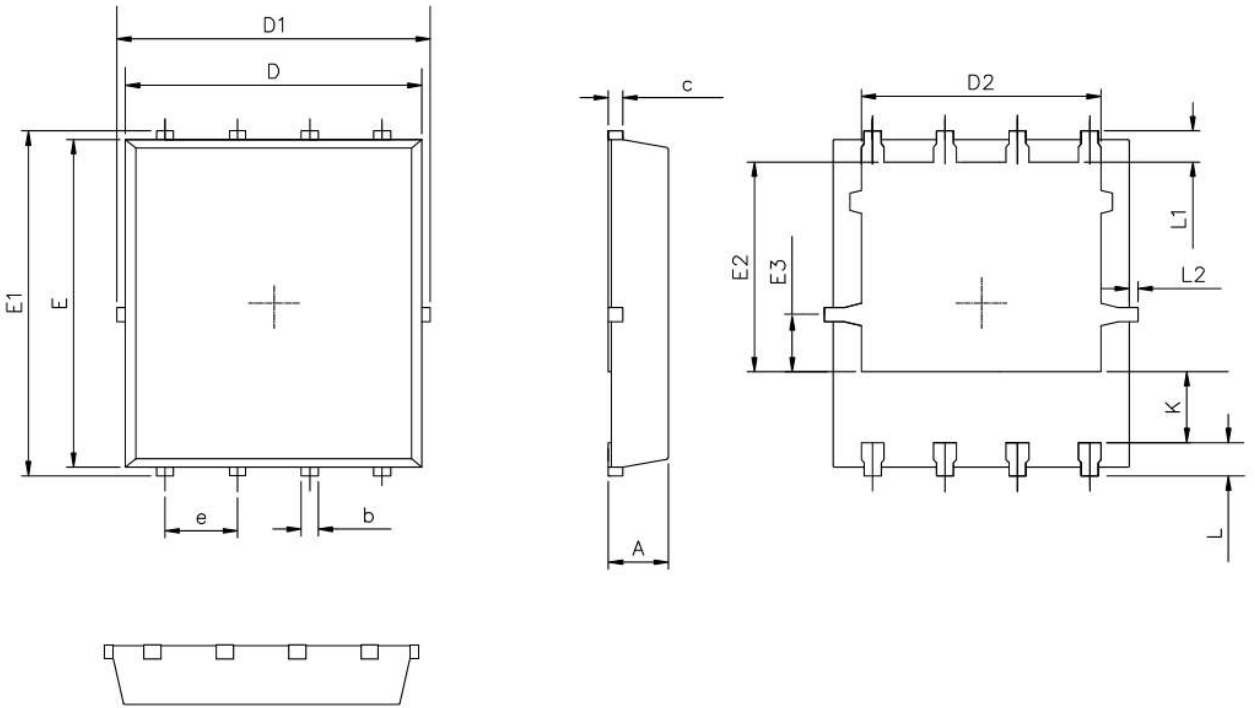
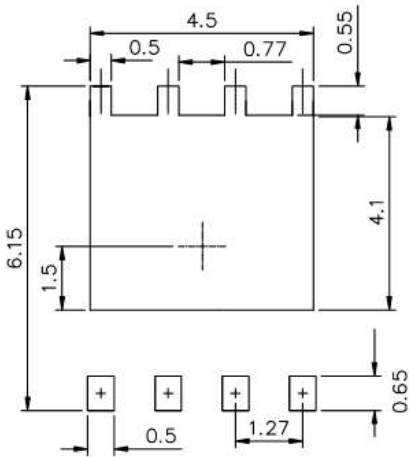


Fig.11 normalized maximum transient thermal impedance

■ PDFN5X6-8L PACEAGE MECHANICAL DATA



RECOMMENDED LAND PATTERN



UNIT:mm

	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50